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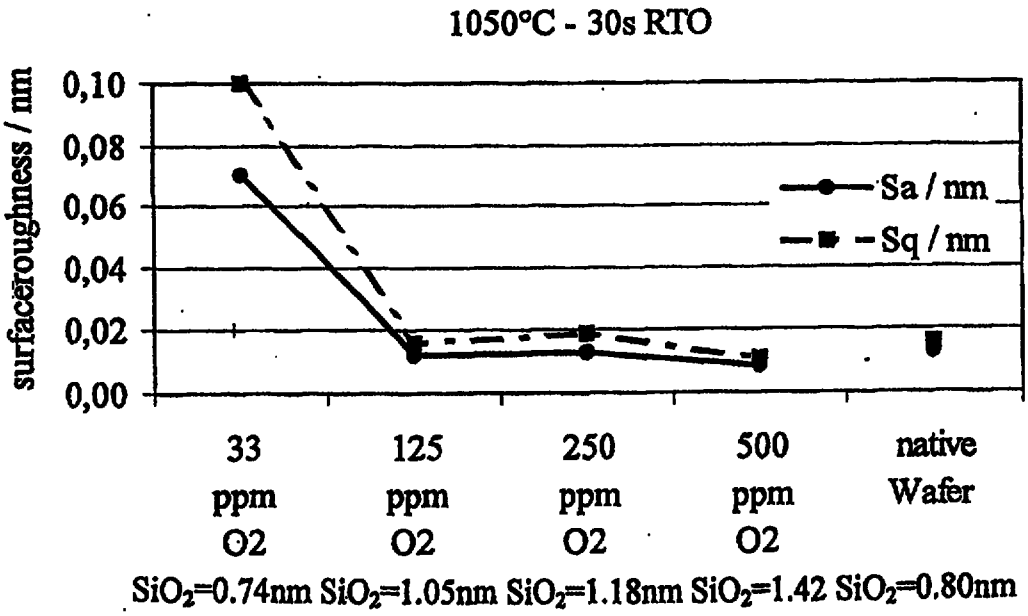
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(54) Title: METHOD FOR RAPID THERMAL PROCESSING (RTP) OF A SILICON SUBSTRATE



(57) Abstract

A method of rapid thermal processing (RTP) of a silicon substrate is presented, where a very low partial pressure of reactive gas is used to control etching and growth of oxides on the silicon surface.